

STP10N95K5-VB Datasheet

N-Channel 650V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V) at T _J max.	900	
R _{DS(on)} at 25 °C (Ω)	V _{GS} = 10 V	0.47
Q _g max. (nC)	73	
Q _{gs} (nC)	9	
Q _{gd} (nC)	17	
Configuration	Single	

FEATURES

- Low figure-of-merit (FOM) R_{on} x Q_g
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

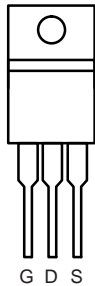
APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting

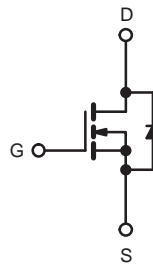


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Top View




N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	900	V	
Gate-Source Voltage		V _{GS}	± 30		
Continuous Drain Current (T _J = 150 °C)	V _{GS} at 10 V	I _D	T _C = 25 °C	11	A
			T _C = 100 °C	8	
Pulsed Drain Current ^a		I _{DM}	28		
Linear Derating Factor			1.4	W/°C	
Single Pulse Avalanche Energy ^b		E _{AS}	226	mJ	
Maximum Power Dissipation		P _D	156	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	
Drain-Source Voltage Slope	T _J = 125 °C	dV/dt	37	V/ns	
Reverse Diode dV/dt ^d			28		
Soldering Recommendations (Peak Temperature) ^c	for 10 s		300	°C	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- V_{DD} = 50 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 4 A.
- 1.6 mm from case.
- I_{SD} ≤ I_D, dI/dt = 100 A/μs, starting T_J = 25 °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.8	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		900	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.78	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}$	-	0.47	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 6\text{ A}$		-	3.5	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	1227	-	pF
Output Capacitance	C_{oss}			-	65	-	
Reverse Transfer Capacitance	C_{rss}			-	4	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	50	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$			-	160	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, V_{DS} = 520\text{ V}$	-	35	73	nC
Gate-Source Charge	Q_{gs}			-	9	-	
Gate-Drain Charge	Q_{gd}			-	17	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 6\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	16	32	ns
Rise Time	t_r			-	19	38	
Turn-Off Delay Time	$t_{d(off)}$			-	35	70	
Fall Time	t_f			-	18	36	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{ open drain}$		-	0.81	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	11	A
Pulsed Diode Forward Current	I_{SM}			-	-	28	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 6\text{ A}, V_{GS} = 0\text{ V}$		-	1.0	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 6\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	309	618	ns
Reverse Recovery Charge	Q_{rr}			-	3.8	7.6	μC
Reverse Recovery Current	I_{RRM}			-	21	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

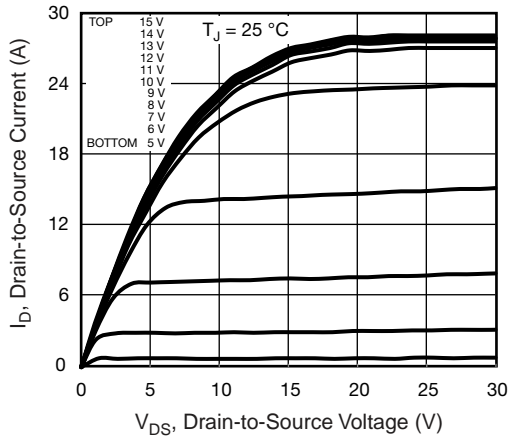


Fig. 1 - Typical Output Characteristics

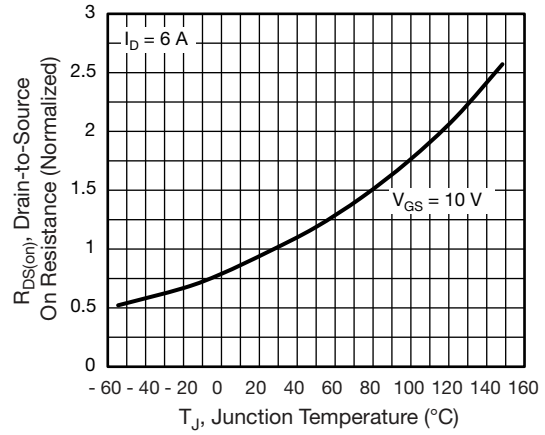


Fig. 4 - Normalized On-Resistance vs. Temperature

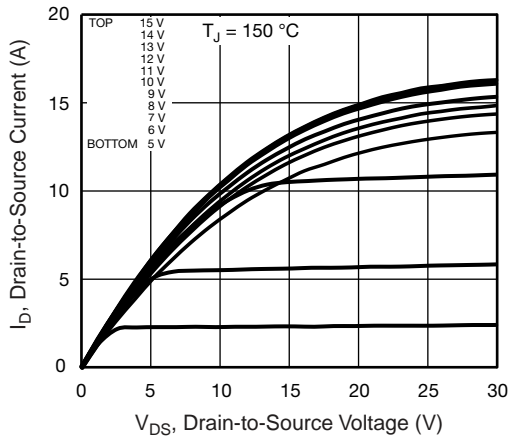


Fig. 2 - Typical Output Characteristics

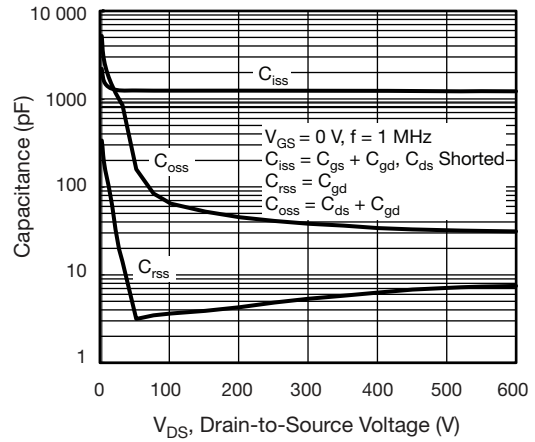


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

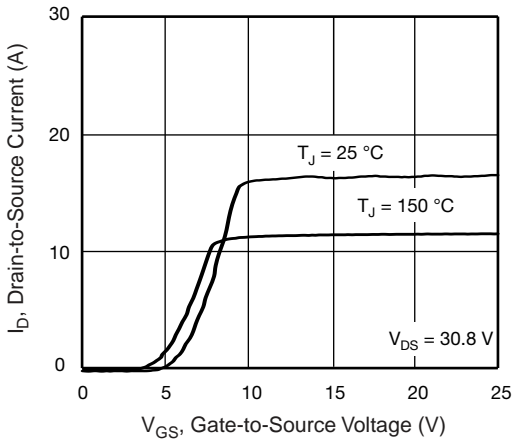


Fig. 3 - Typical Transfer Characteristics

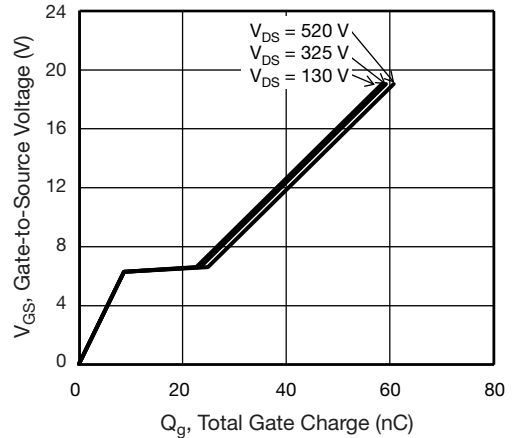


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

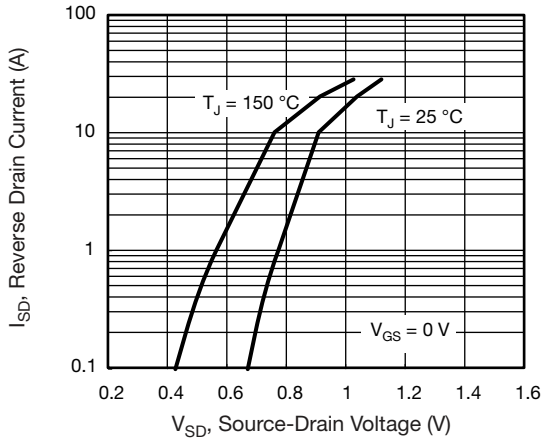


Fig. 7 - Typical Source-Drain Diode Forward Voltage

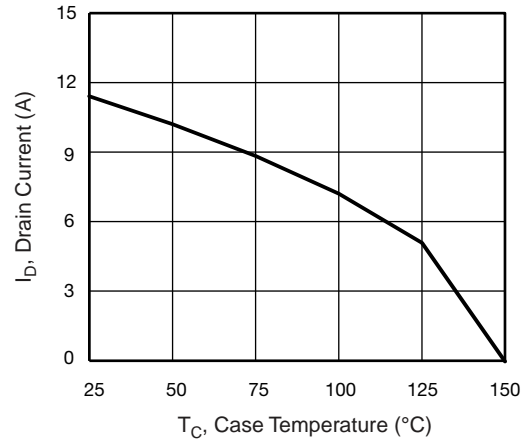


Fig. 9 - Maximum Drain Current vs. Case Temperature

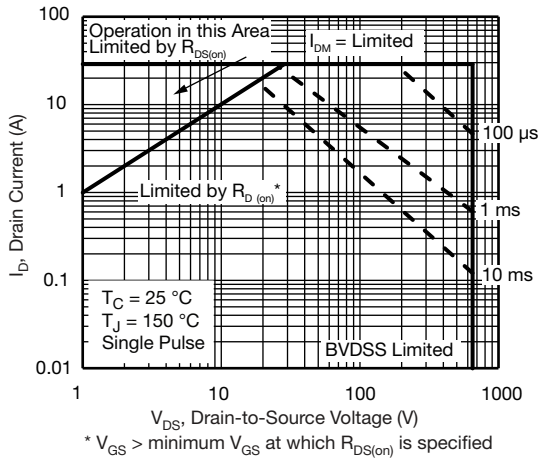


Fig. 8 - Maximum Safe Operating Area

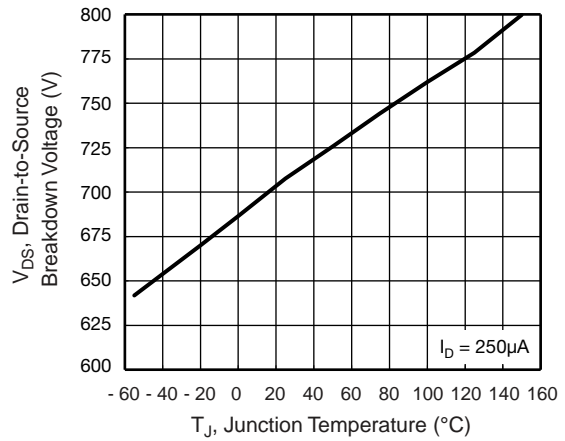


Fig. 10 - Temperature vs. Drain-to-Source Voltage

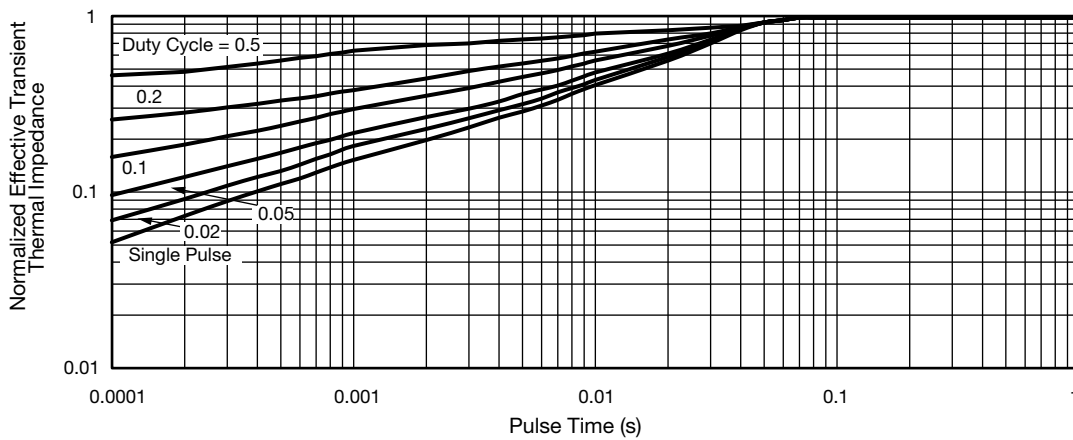


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

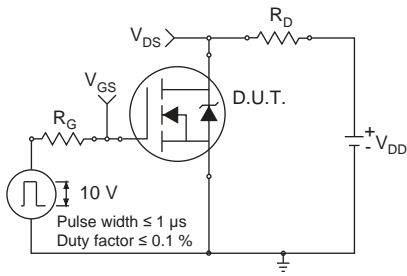


Fig. 12 - Switching Time Test Circuit

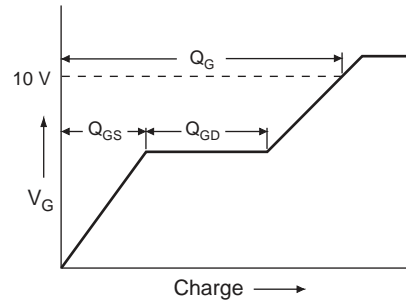


Fig. 16 - Basic Gate Charge Waveform

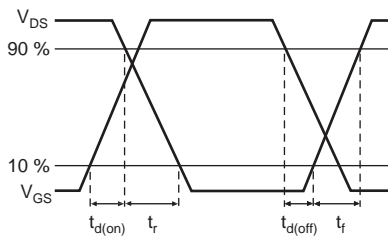


Fig. 13 - Switching Time Waveforms

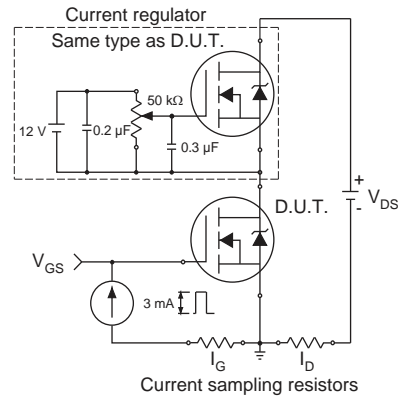


Fig. 17 - Gate Charge Test Circuit

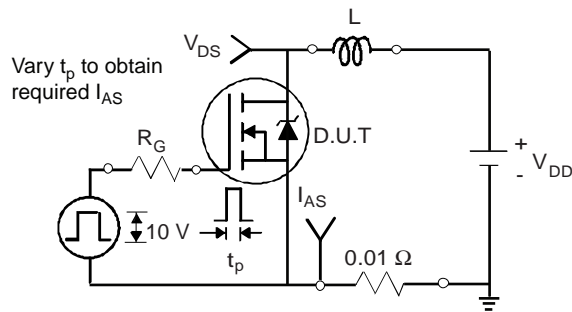


Fig. 14 - Unclamped Inductive Test Circuit

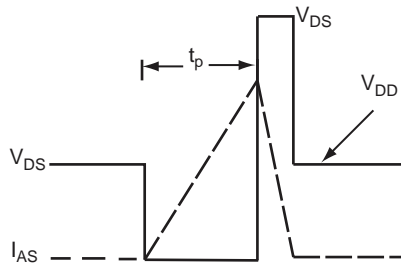
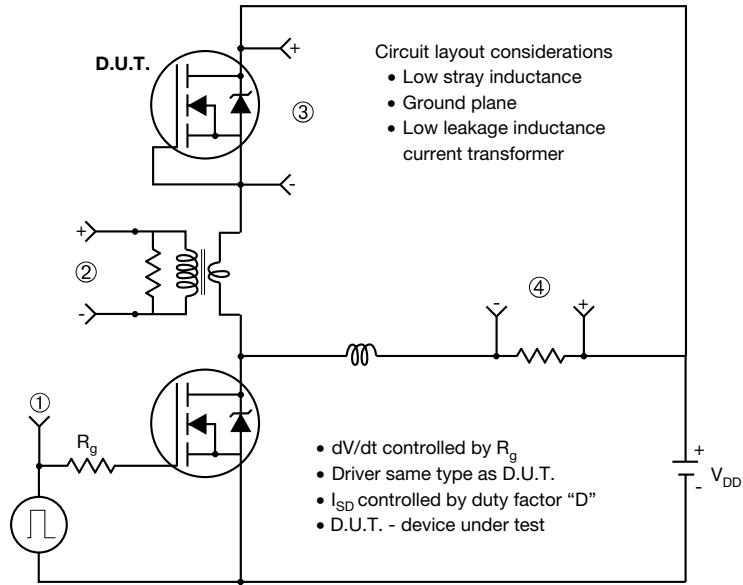


Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery dV/dt Test Circuit

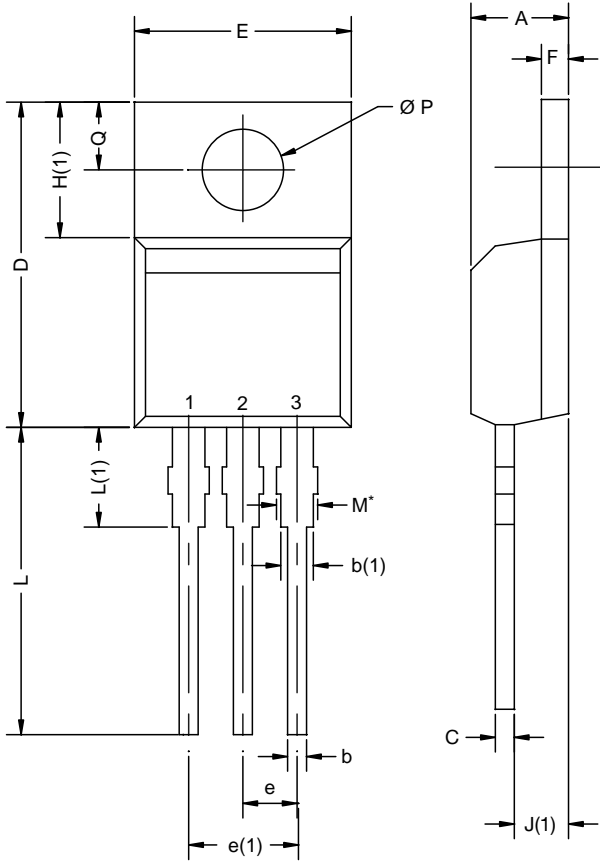


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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